Silicon PNP Power Transistors 2N3791 2N3792

DESCRIPTION

- ·With TO-3 package
- ·Complement to type 2N3715 ,2N3716
- ·Excellent safe operating area

APPLICATIONS

Designed for medium-speed switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

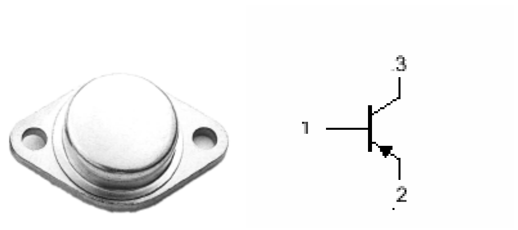

Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N3791	Open emitter	-60	V
		2N3792		-80	
V_{CEO}	Collector-emitter voltage	2N3791	Open base	-60	V
		2N3792		-80	
V_{EBO}	Emitter-base voltage		Open collector	-7	V
I_C	Collector current			-10	A
I_B	Base current			-4	A
P_D	Total Power Dissipation		T_C=25□	150	W
T_j	Junction temperature			200	□
T_{stg}	Storage temperature			-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{(th)\ jc}$	Thermal resistance junction to case	1.17	□/W

CHARACTERISTICS

T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N3791	I_C=-0.2A ;I_B=0	-60			V
		2N3792		-80			V
$V_{CE(sat)}$	Collector-emitter saturation voltage		I_C=-5A; I_B=-0.5A			-1.0	V
$V_{BE(on)-1}$	Base-emitter on voltage		I_C=-5A ; V_{CE}=-2V			-1.8	V
$V_{BE(on)-2}$	Base-emitter on voltage		I_C=-10A ; V_{CE}=-4V			-4.0	V
I_{CEX}	Collector cut-off current	2N3791	V_{CE}=-60V; $V_{BE(off)}$=-1.5V T_C=150℃			-1.0 -5.0	mA
		2N3792	V_{CE}=-80V; $V_{BE(off)}$=-1.5V T_C=150℃			-1.0 -5.0	mA
I_{EBO}	Emitter cut-off current		V_{EB}=-7V; I_C=0			-5.0	mA
h_{FE-1}	DC current gain		I_C=-1A ; V_{CE}=-2V	50		180	
h_{FE-2}	DC current gain		I_C=-3A ; V_{CE}=-2V	30			
f_T	Transition frequency		I_C=-0.5A;V_{CE}=-10V	4			MHz

PACKAGE OUTLINE

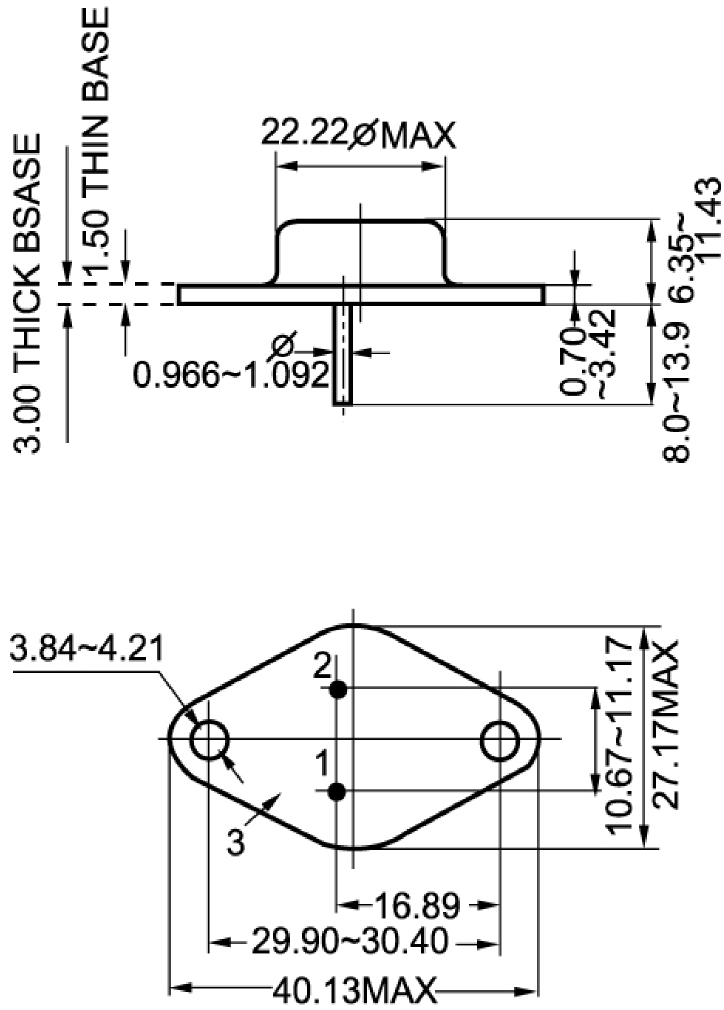

Fig.2 outline dimensions (unindicated tolerance:±0.10mm)